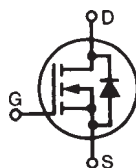


**TrenchT2™ Power
MOSFET**
IXTH260N055T2

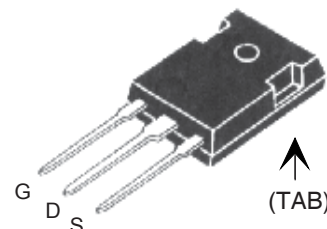
$$V_{DSS} = 55V$$

$$I_{D25} = 260A$$

$$R_{DS(on)} \leq 3.3m\Omega$$

 N-Channel Enhancement Mode
Avalanche Rated


TO-247


 G = Gate D = Drain
S = Source TAB = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 55 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 55 | V |
| V_{GSM} | Transient | ± 20 | V |
| I_{D25} | $T_C = 25^\circ C$ | 260 | A |
| I_{LRMS} | Lead Current Limit, RMS | 160 | A |
| I_{DM} | $T_C = 25^\circ C$, pulse width limited by T_{JM} | 780 | A |
| I_A | $T_C = 25^\circ C$ | 100 | A |
| E_{AS} | $T_C = 25^\circ C$ | 600 | mJ |
| P_D | $T_C = 25^\circ C$ | 480 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | 1.6mm (0.062in.) from case for 10s | 300 | $^\circ C$ |
| T_{sold} | Plastic body for 10 seconds | 260 | $^\circ C$ |
| M_d | Mounting torque | 1.13 / 10 | Nm/lb.in. |
| Weight | | 6 | g |

Features

- International standard package
- $175^\circ C$ Operating Temperature
- High current handling capability
- Avalanche rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

| Symbol | Test Conditions ($T_J = 25^\circ C$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 55 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.0 | | 4.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 5 μA |
| | $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 150 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2 | | | 3.3 $m\Omega$ |

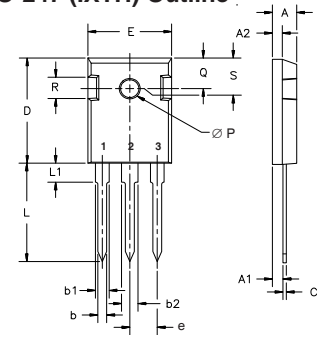
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1 | 55 | 94 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 10.8 | nF |
| C_{oss} | | | 1460 | pF |
| C_{rss} | | | 215 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 100\text{A}$ $R_G = 2\Omega$ (External) | | 20 | ns |
| t_r | | | 27 | ns |
| $t_{d(off)}$ | | | 36 | ns |
| t_f | | | 24 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 140 | nC |
| Q_{gs} | | | 52 | nC |
| Q_{gd} | | | 32 | nC |
| R_{thJC} | | | 0.31 | $^\circ\text{C/W}$ |
| R_{thCH} | | 0.21 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|--------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 260 A |
| I_{SM} | Repetitive, Pulse width limited by T_{JM} | | | 1000 A |
| V_{SD} | $I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.3 V |
| t_{rr} | $I_F = 130\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 27\text{V}$ | | 60 | ns |
| I_{RM} | | | 3.4 | A |
| Q_{RM} | | | 102 | nC |

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

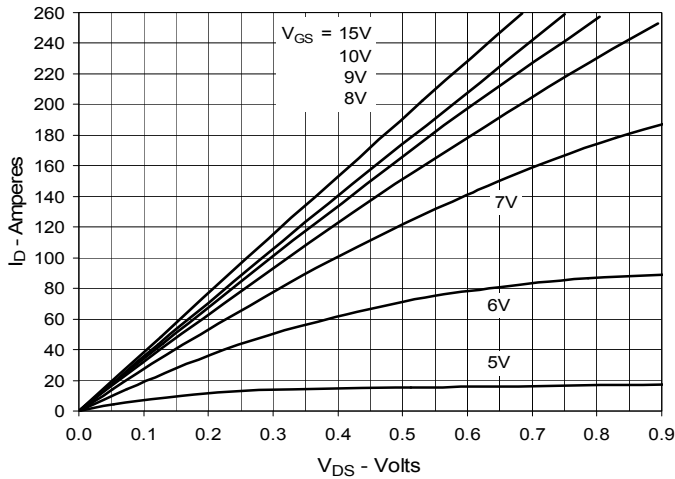


Fig. 2. Extended Output Characteristics @ 25°C

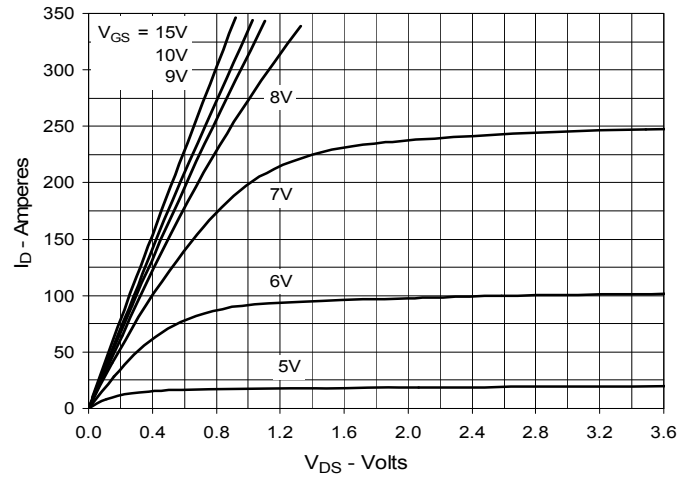


Fig. 3. Output Characteristics @ 150°C

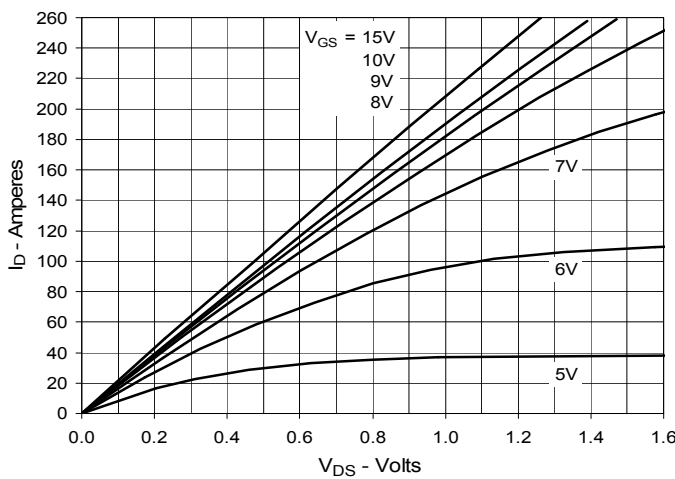


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 130A$ Value vs. Junction Temperature

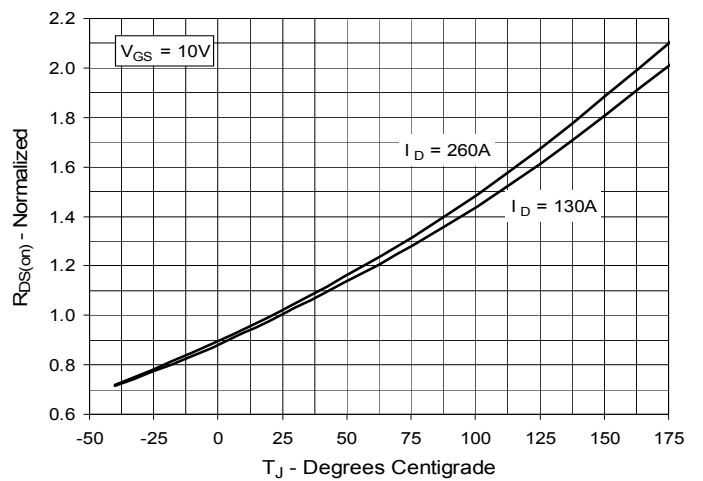


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 130A$ Value vs. Drain Current

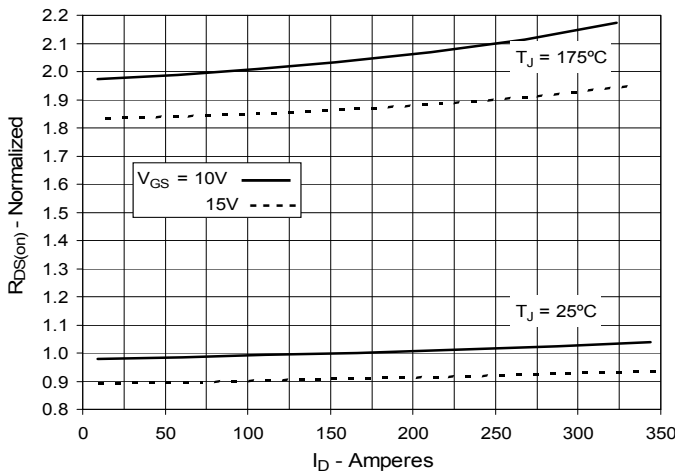


Fig. 6. Drain Current vs. Case Temperature

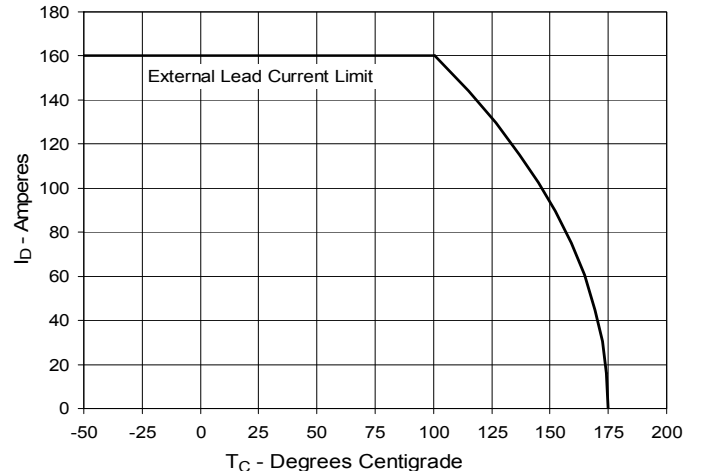


Fig. 7. Input Admittance

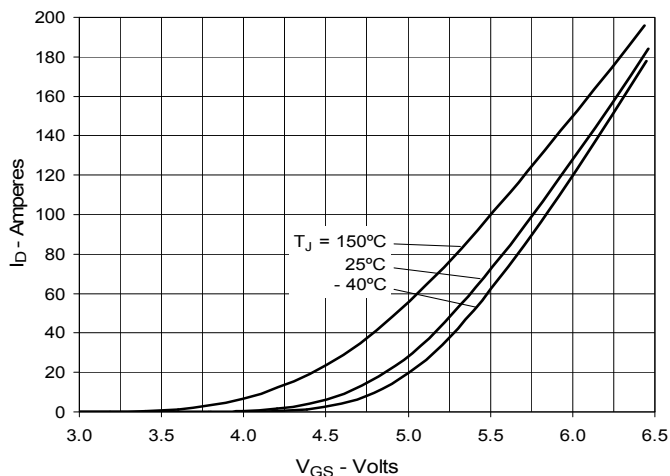


Fig. 8. Transconductance

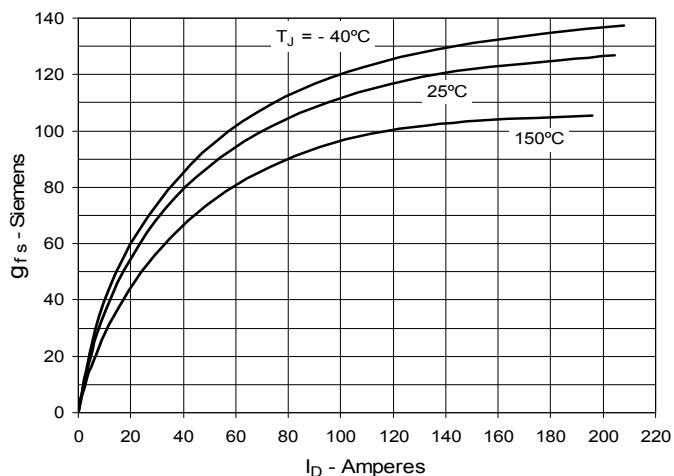


Fig. 9. Forward Voltage Drop of Intrinsic Diode

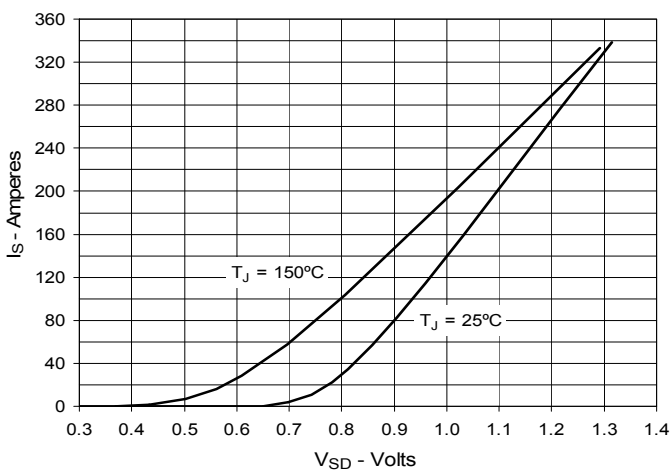


Fig. 10. Gate Charge

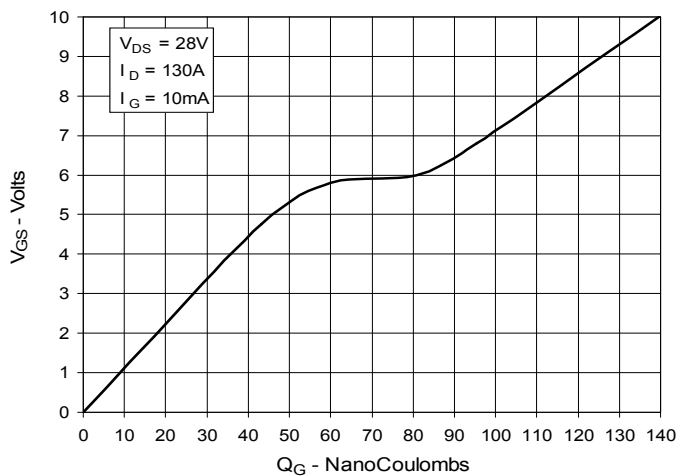


Fig. 11. Capacitance

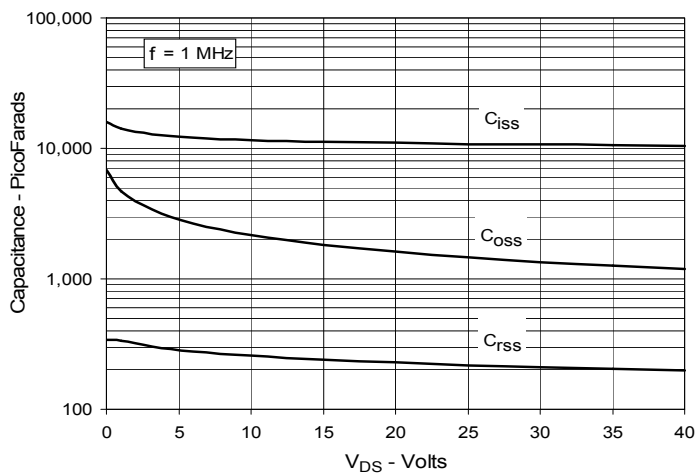


Fig. 12. Forward-Bias Safe Operating Area

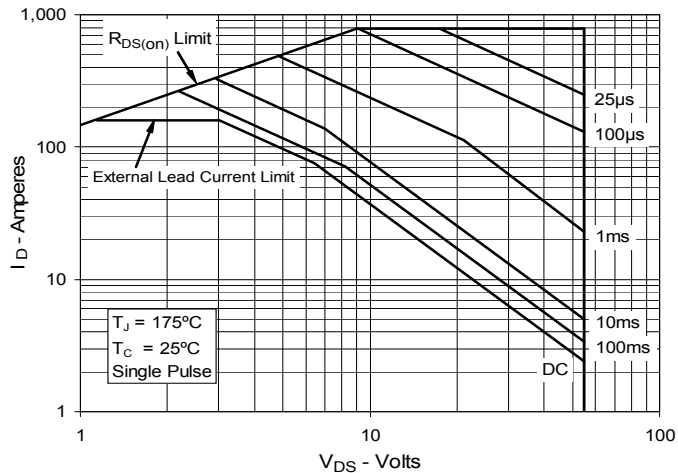


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

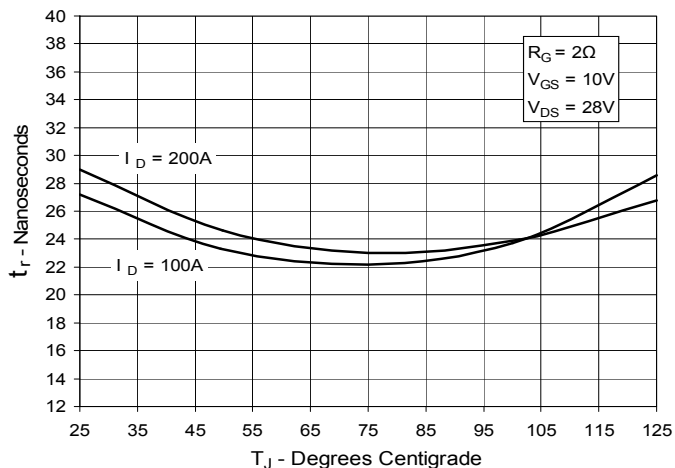


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

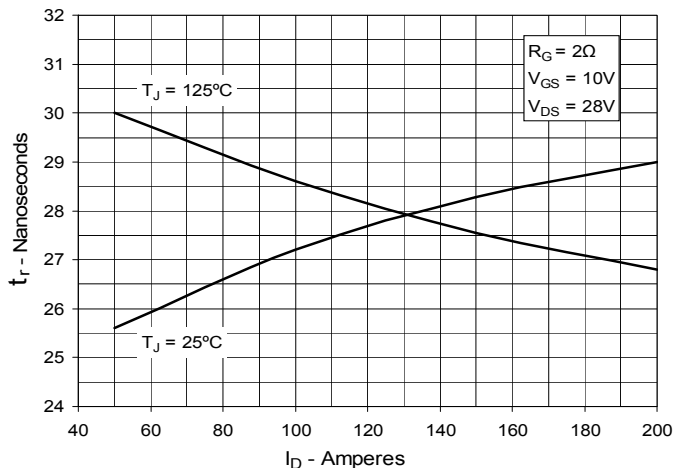


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

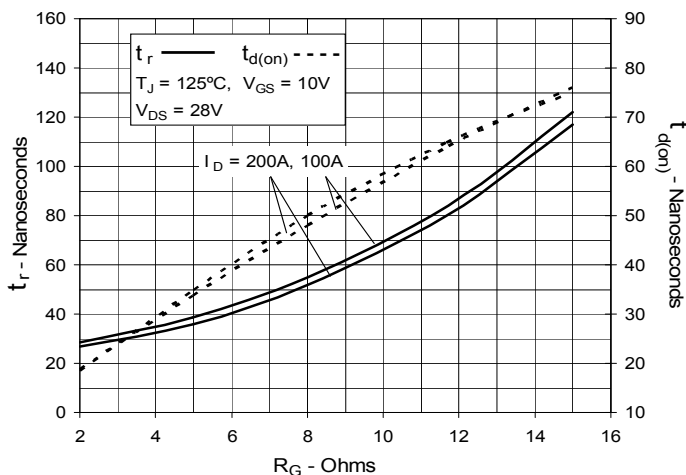


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

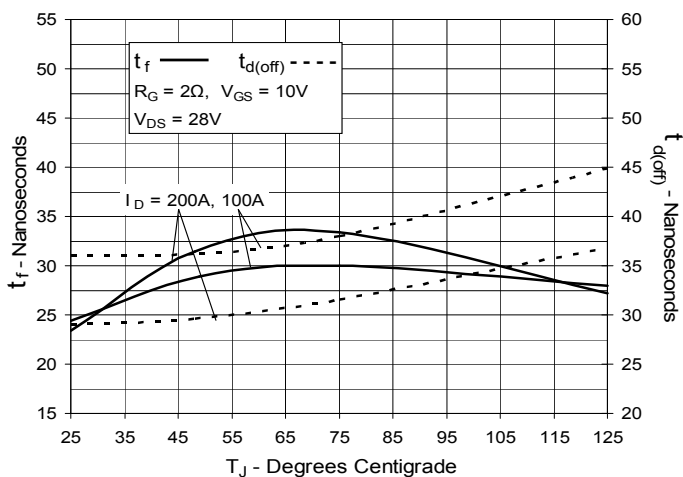


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

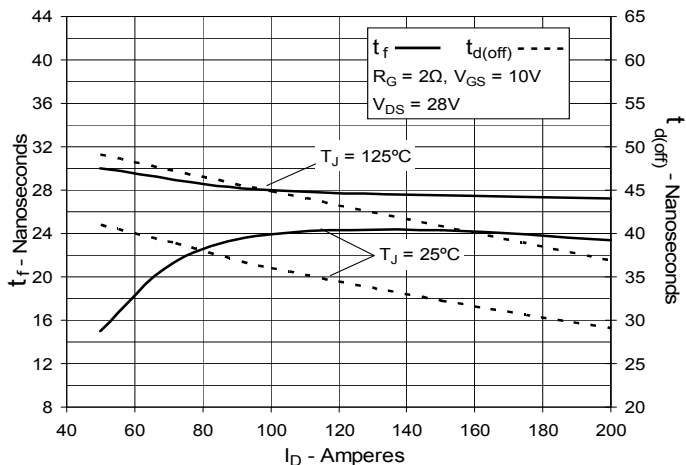


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

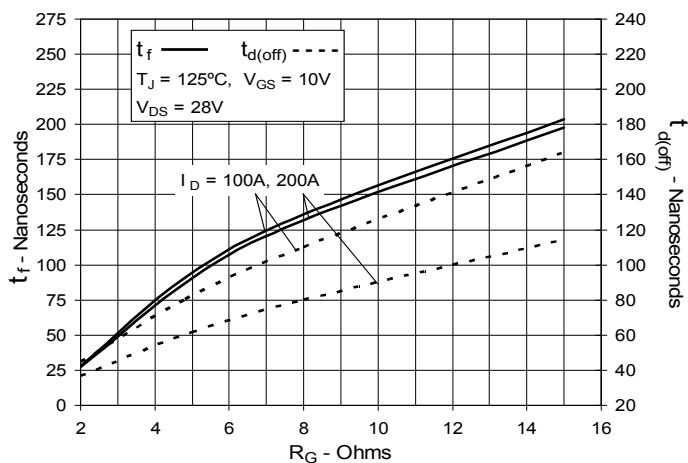
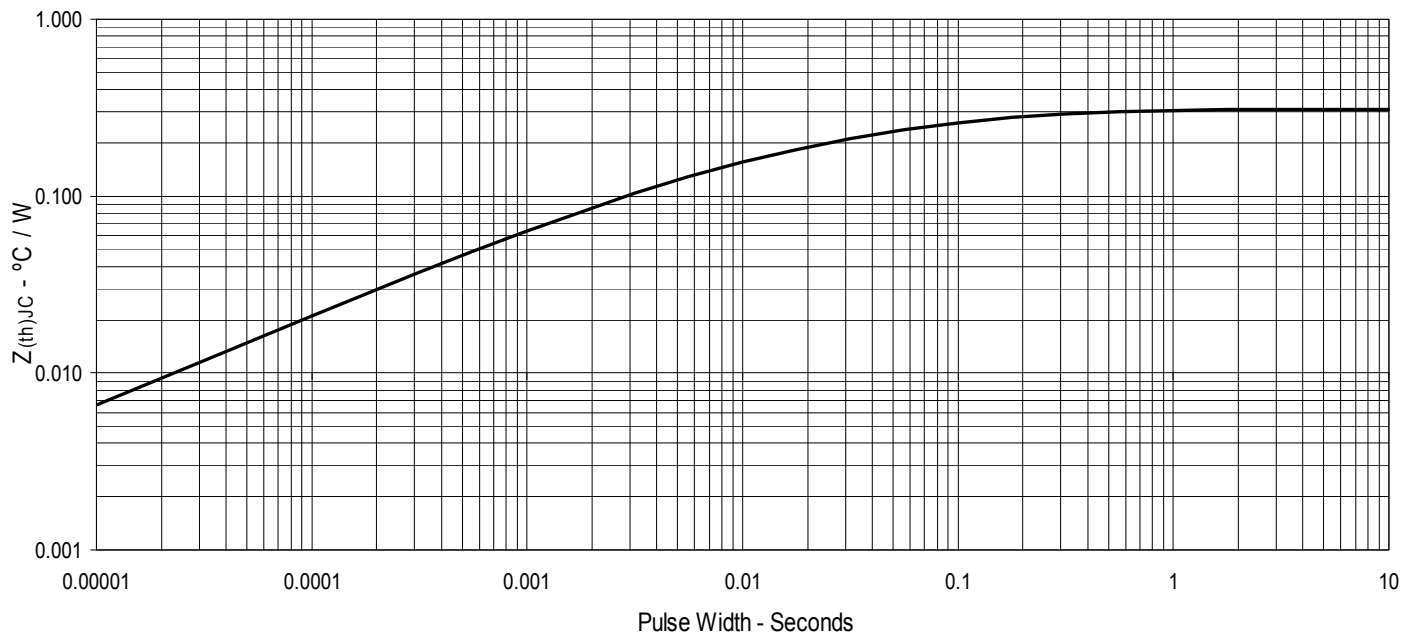


Fig. 19. Maximum Transient Thermal Impedance





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